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Article

Exceedingly High Performance Top-Gate P-Type SnO Thin Film Transistor with a Nanometer Scale Channel Layer

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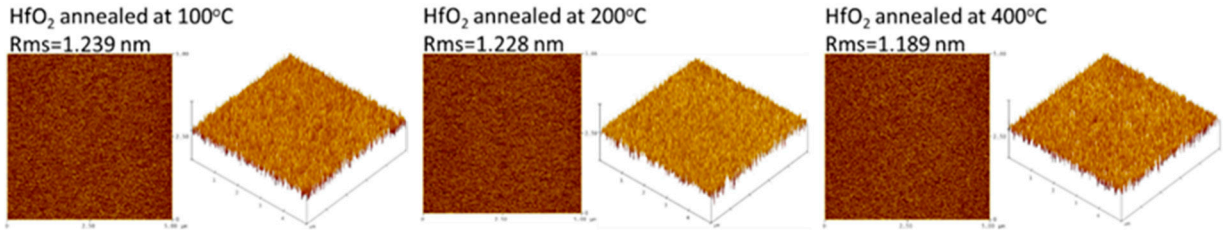
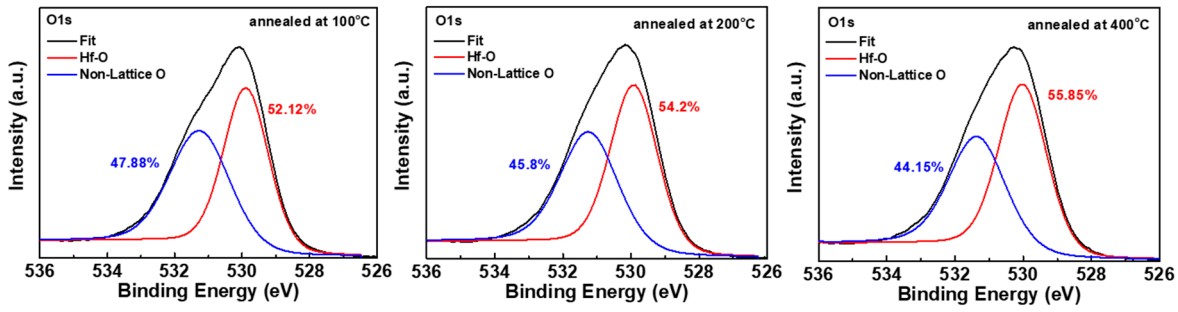


(a) (b) (c)

Figure S1. The surface roughness analysis of HfO_2 annealed at (a) 100 °C, (b) 200 °C and (c) 400 °C through AFM.



(a) (b) (c)

Figure S2. The O_{1s} spectra of HfO_2 films annealed at (a) 100°C, (b) 200°C and (c) 400°C.